

# MMBF5460LT1

## JFET - General Purpose Transistor

### P-Channel

#### Features

- Pb-Free Package is Available

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	$V_{DG}$	40	Vdc
Reverse Gate-Source Voltage	$V_{GSR}$	40	Vdc
Forward Gate Current	$I_{GF}$	10	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

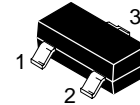
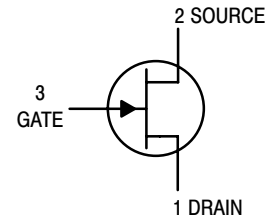
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.



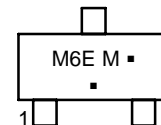
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SOT-23 (TO-236)  
CASE 318  
STYLE 10

#### MARKING DIAGRAM



M6E = Device Code  
M = Date Code\*  
■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBF5460LT1	SOT-23	3,000 / Tape & Reel
MMBF5460LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

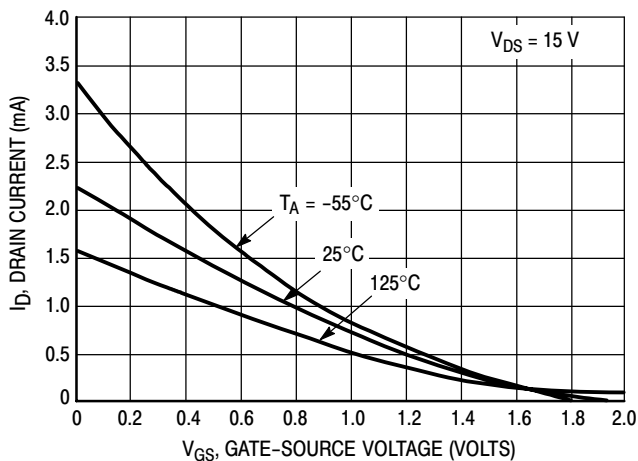
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBF5460LT1

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

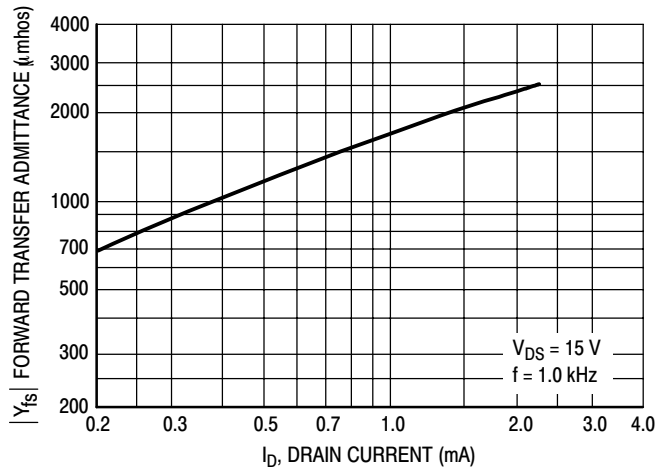
Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Gate–Source Breakdown Voltage ( $I_G = 10 \mu\text{Adc}$ , $V_{DS} = 0$ )	$V_{(BR)GSS}$	40	–	–	Vdc
Gate Reverse Current ( $V_{GS} = 20 \text{Vdc}$ , $V_{DS} = 0$ ) ( $V_{GS} = 20 \text{Vdc}$ , $V_{DS} = 0$ , $T_A = 100^\circ\text{C}$ )	$I_{GSS}$	–	–	5.0 1.0	nAdc $\mu\text{Adc}$
Gate Source Cutoff Voltage ( $V_{DS} = 15 \text{Vdc}$ , $I_D = 1.0 \mu\text{Adc}$ )	$V_{GS(off)}$	0.75	–	6.0	Vdc
Gate Source Voltage ( $V_{DS} = 15 \text{Vdc}$ , $I_D = 0.1 \text{mAdc}$ )	$V_{GS}$	0.5	–	4.0	Vdc
<b>ON CHARACTERISTICS</b>					
Zero–Gate–Voltage Drain Current ( $V_{DS} = 15 \text{Vdc}$ , $V_{GS} = 0$ )	$I_{DSS}$	–1.0	–	–5.0	mAdc
<b>SMALL–SIGNAL CHARACTERISTICS</b>					
Forward Transfer Admittance ( $V_{DS} = 15 \text{Vdc}$ , $V_{GS} = 0$ , $f = 1.0 \text{kHz}$ )	$ Y_{fs} $	1000	–	4000	$\mu\text{mhos}$
Output Admittance ( $V_{DS} = 15 \text{Vdc}$ , $V_{GS} = 0$ , $f = 1.0 \text{kHz}$ )	$ Y_{os} $	–	–	75	$\mu\text{mhos}$
Input Capacitance ( $V_{DS} = 15 \text{Vdc}$ , $V_{GS} = 0$ , $f = 1.0 \text{MHz}$ )	$C_{iss}$	–	5.0	7.0	pF
Reverse Transfer Capacitance ( $V_{DS} = 15 \text{Vdc}$ , $V_{GS} = 0$ , $f = 1.0 \text{MHz}$ )	$C_{rss}$	–	1.0	2.0	pF

**DRAIN CURRENT versus GATE SOURCE VOLTAGE**

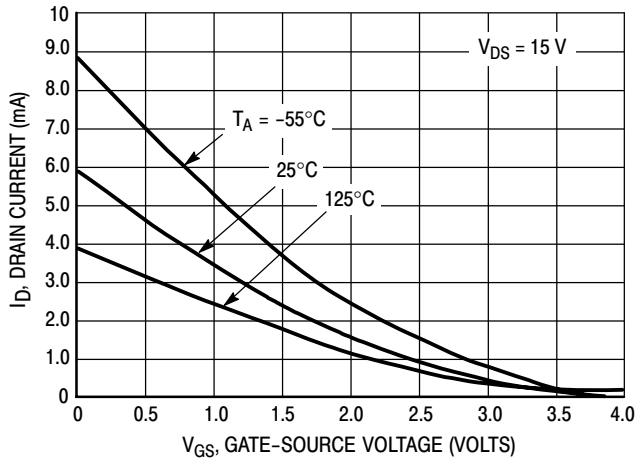


**Figure 1.  $V_{GS(off)} = 2.0$  Volts**

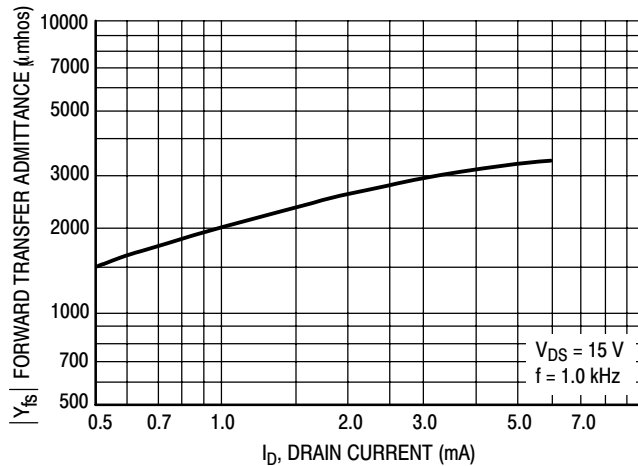
**FORWARD TRANSFER ADMITTANCE versus DRAIN CURRENT**



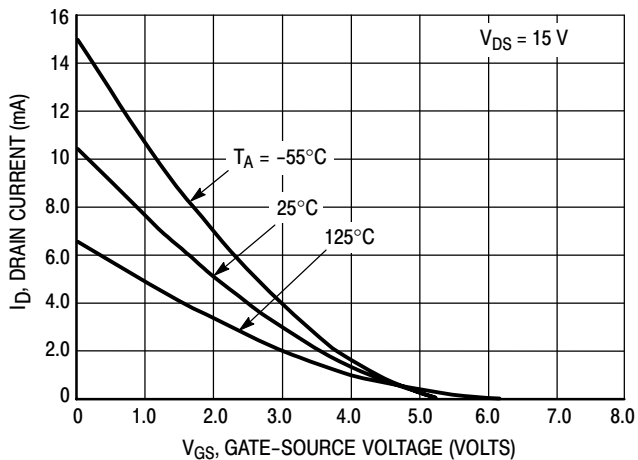
**Figure 4.  $V_{GS(off)} = 2.0$  Volts**



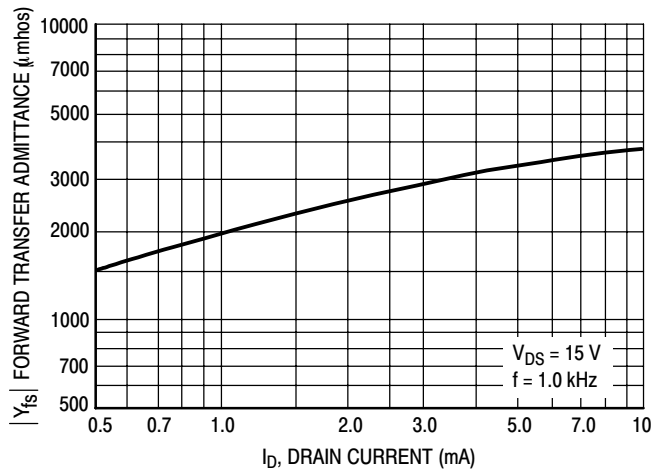
**Figure 2.  $V_{GS(off)} = 4.0$  Volts**



**Figure 5.  $V_{GS(off)} = 4.0$  Volts**

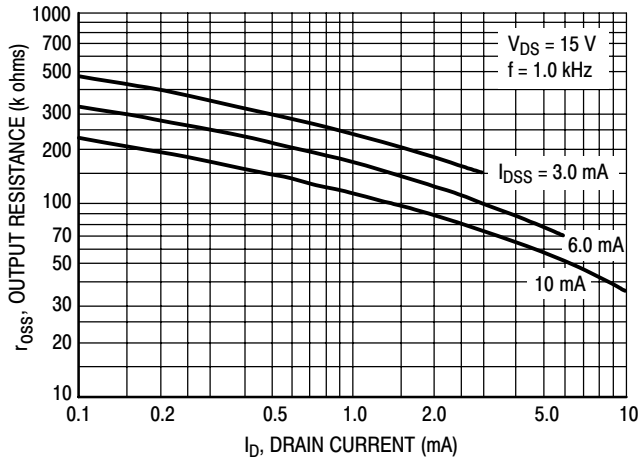


**Figure 3.  $V_{GS(off)} = 5.0$  Volts**

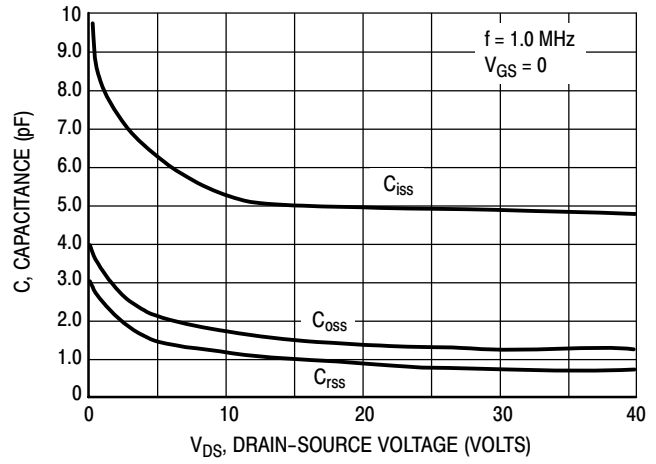


**Figure 6.  $V_{GS(off)} = 5.0$  Volts**

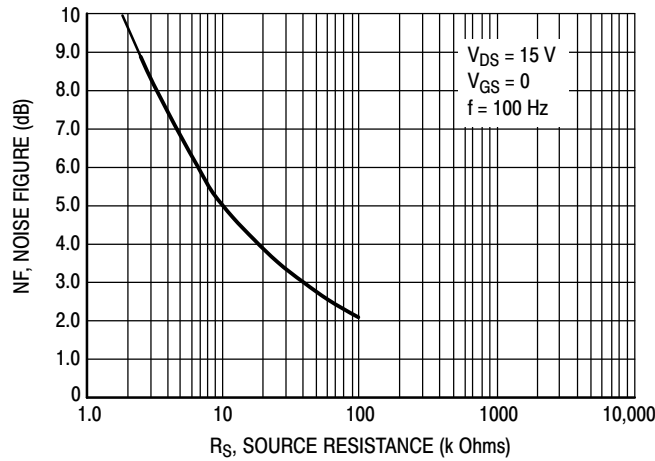
# MMBF5460LT1



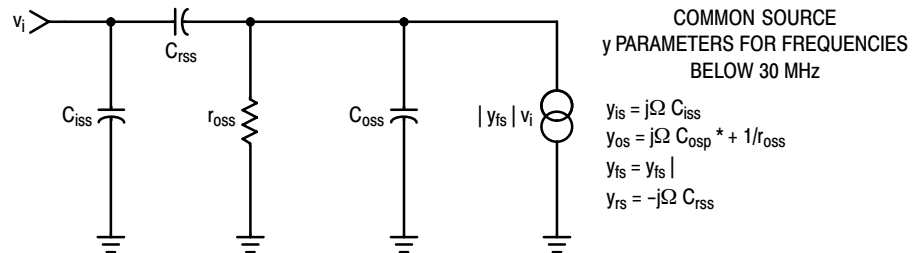
**Figure 7. Output Resistance versus Drain Current**



**Figure 8. Capacitance versus Drain-Source Voltage**



**Figure 9. Noise Figure versus Source Resistance**



COMMON SOURCE  
y PARAMETERS FOR FREQUENCIES  
BELOW 30 MHz

$$y_{is} = j\Omega C_{iss}$$

$$y_{os} = j\Omega C_{osp} + 1/r_{oss}$$

$$y_{fs} = y_{ts}$$

$$y_{rs} = -j\Omega C_{rss}$$

\* $C_{osp}$  is  $C_{oss}$  in parallel with Series Combination of  $C_{iss}$  and  $C_{rss}$ .

NOTE:

- Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%).

**Figure 10. Equivalent Low Frequency Circuit**

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

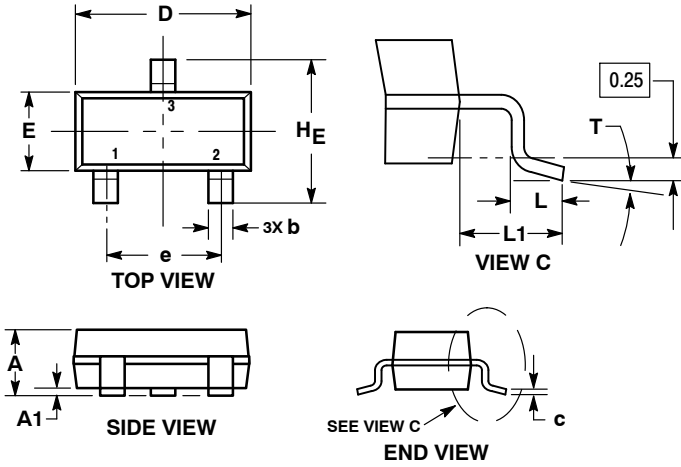
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### SOT-23 (TO-236) CASE 318-08 ISSUE AS

DATE 30 JAN 2018

SCALE 4:1

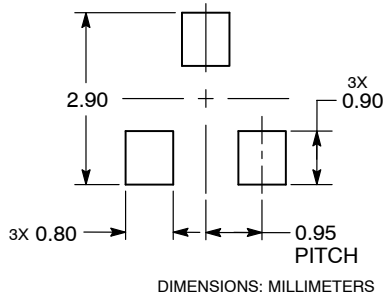


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

### RECOMMENDED SOLDERING FOOTPRINT



### GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:  
CANCELLED

STYLE 6:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 7:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 8:  
PIN 1. ANODE  
2. NO CONNECTION  
3. CATHODE

STYLE 9:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 10:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE

STYLE 11:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE-ANODE

STYLE 12:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 13:  
PIN 1. SOURCE  
2. DRAIN  
3. GATE

STYLE 14:  
PIN 1. CATHODE  
2. GATE  
3. ANODE

STYLE 15:  
PIN 1. GATE  
2. CATHODE  
3. ANODE

STYLE 16:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE

STYLE 17:  
PIN 1. NO CONNECTION  
2. ANODE  
3. CATHODE

STYLE 18:  
PIN 1. NO CONNECTION  
2. CATHODE  
3. ANODE

STYLE 19:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE-ANODE

STYLE 20:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

STYLE 21:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 22:  
PIN 1. RETURN  
2. OUTPUT  
3. INPUT

STYLE 23:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 24:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE

STYLE 25:  
PIN 1. ANODE  
2. CATHODE  
3. GATE

STYLE 26:  
PIN 1. CATHODE  
2. ANODE  
3. NO CONNECTION

STYLE 27:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE

STYLE 28:  
PIN 1. ANODE  
2. ANODE  
3. ANODE

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